

Description

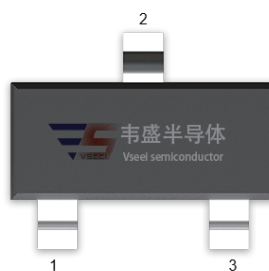
The VSM3407D uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.

General Features

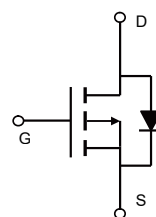
- $V_{DS} = -30V, I_D = -3.9A$
 $R_{DS(ON)} = 38m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} = 62m\Omega @ V_{GS} = -4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



SOT-23



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM3407D	VSM3407D-S2	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-3.9	A
Drain Current-Pulsed (Note 1)	I_{DM}	-15.6	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89	$^\circ C/W$
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Electrical Characteristics ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$	-	-	-1	μA

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-1.1	-1.6	-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-3A	-	38	46	mΩ
		V _{GS} =-4.5V, I _D =-2A	-	62	80	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V,I _D =-3A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-15V,V _{GS} =0V, F=1.0MHz	-	523	-	PF
Output Capacitance	C _{oss}		-	78	-	PF
Reverse Transfer Capacitance	C _{rss}		-	61	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V,R _L =5Ω V _{GS} =-10V,R _{GEN} =3Ω	-	8.5	-	nS
Turn-on Rise Time	t _r		-	5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	26	-	nS
Turn-Off Fall Time	t _f		-	13	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V,I _D =-3A,V _{GS} =-10V	-	11.5	-	nC
Gate-Source Charge	Q _{gs}		-	2.8	-	nC
Gate-Drain Charge	Q _{gd}		-	1.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-3A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-3.9	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =-3A	-	11.2	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs(Note3)	-	5.5	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

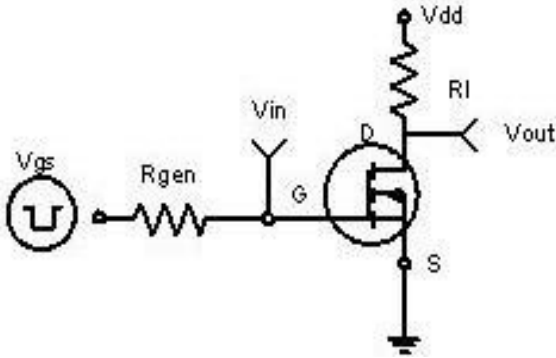


Figure 1: Switching Test Circuit

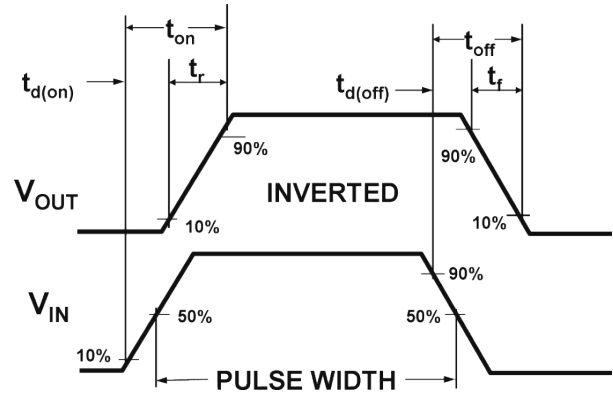


Figure 2: Switching Waveforms

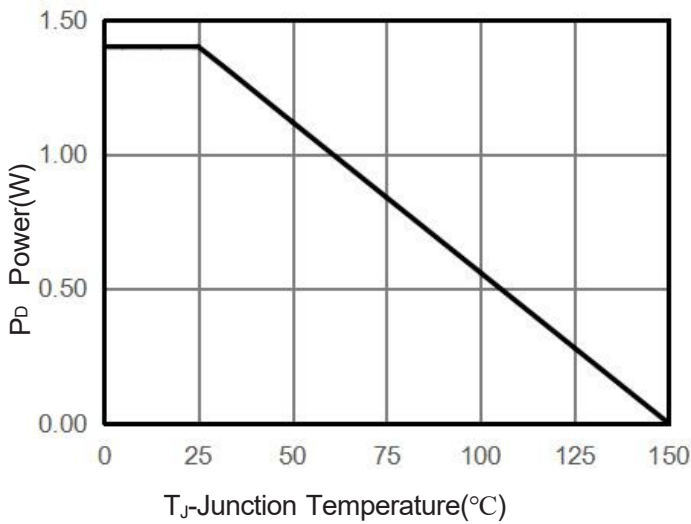


Figure 3 Power Dissipation

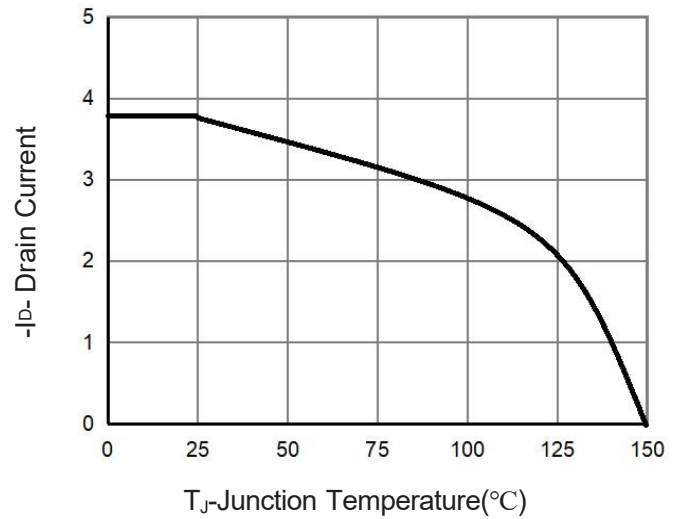


Figure 4 Drain Current

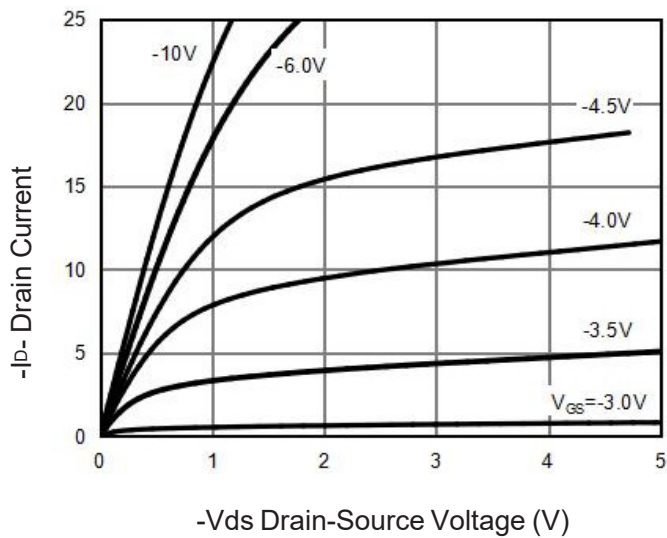


Figure 5 Output Characteristics

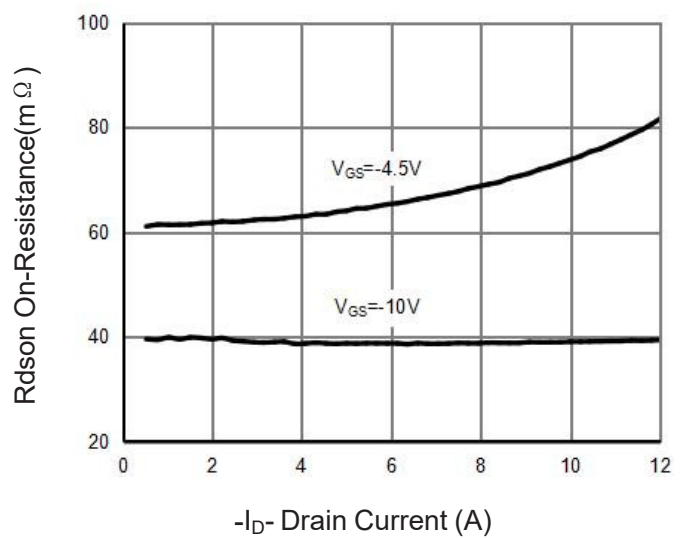
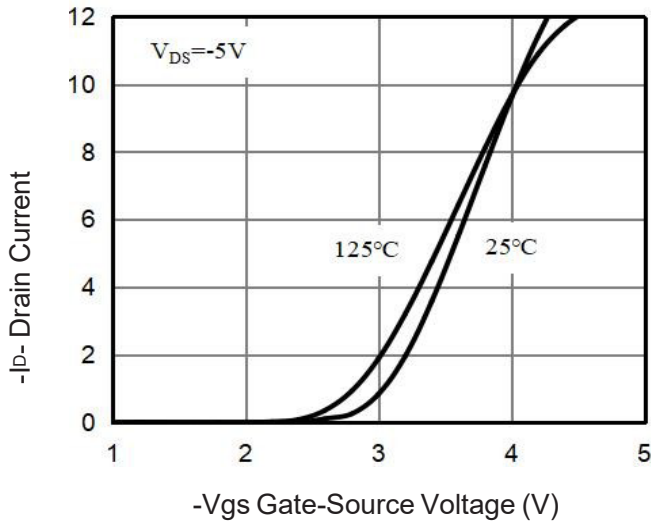
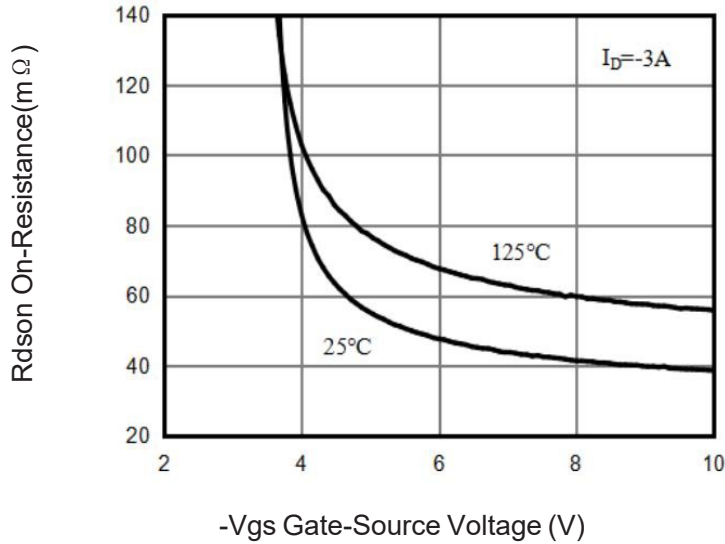
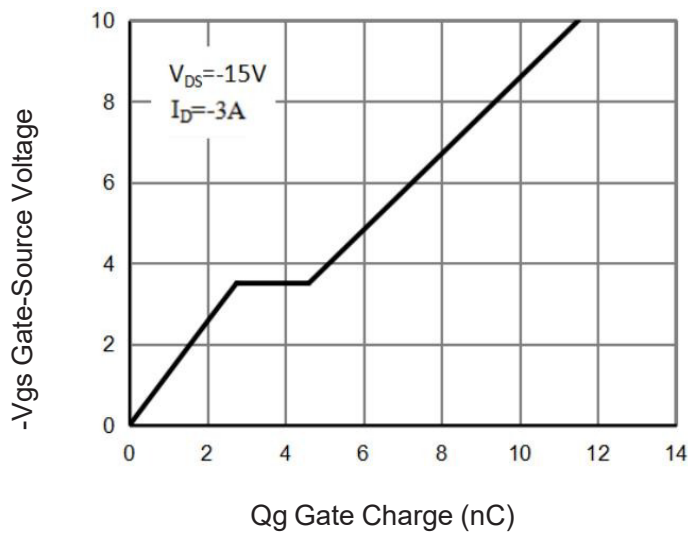
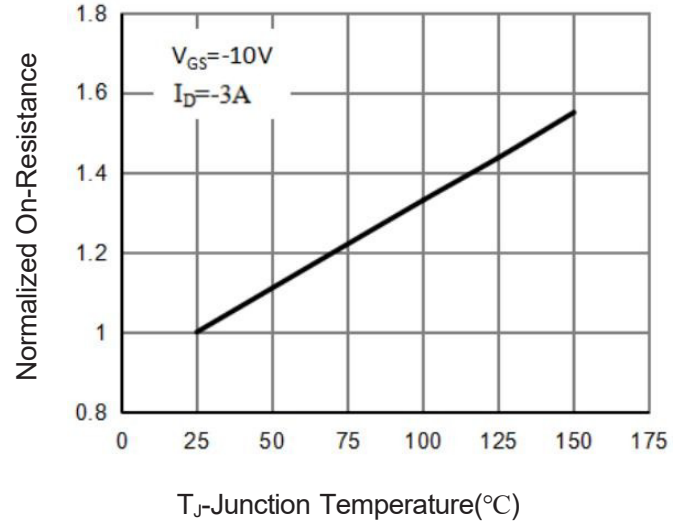
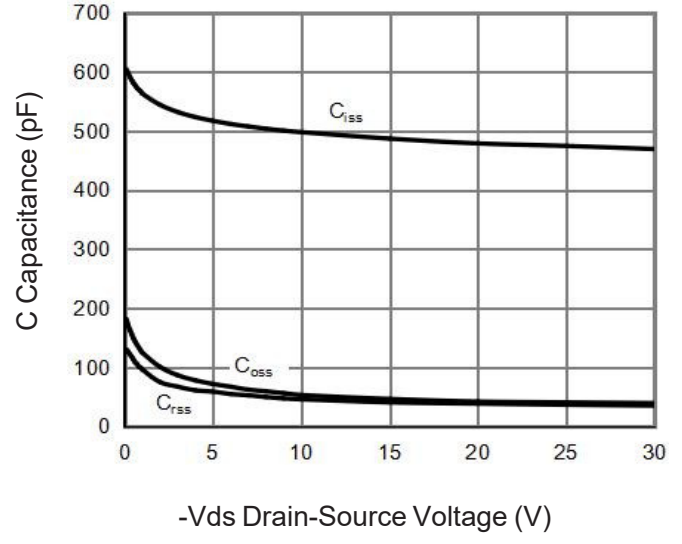
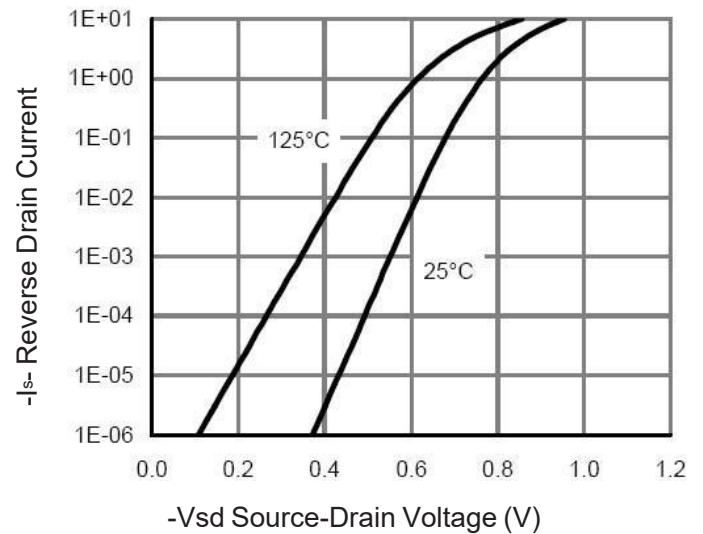


Figure 6 Drain-Source On-Resistance


Figure 7 Transfer Characteristics

Figure 9 Rdson vs Vgs

Figure 11 Gate Charge

Figure 8 Drain-Source On-Resistance

Figure 10 Capacitance vs Vds

Figure 12 Source- Drain Diode Forward

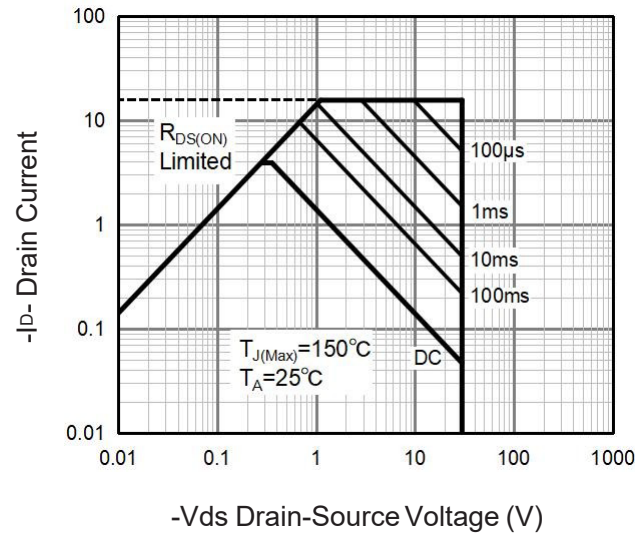


Figure 13 Safe Operation Area

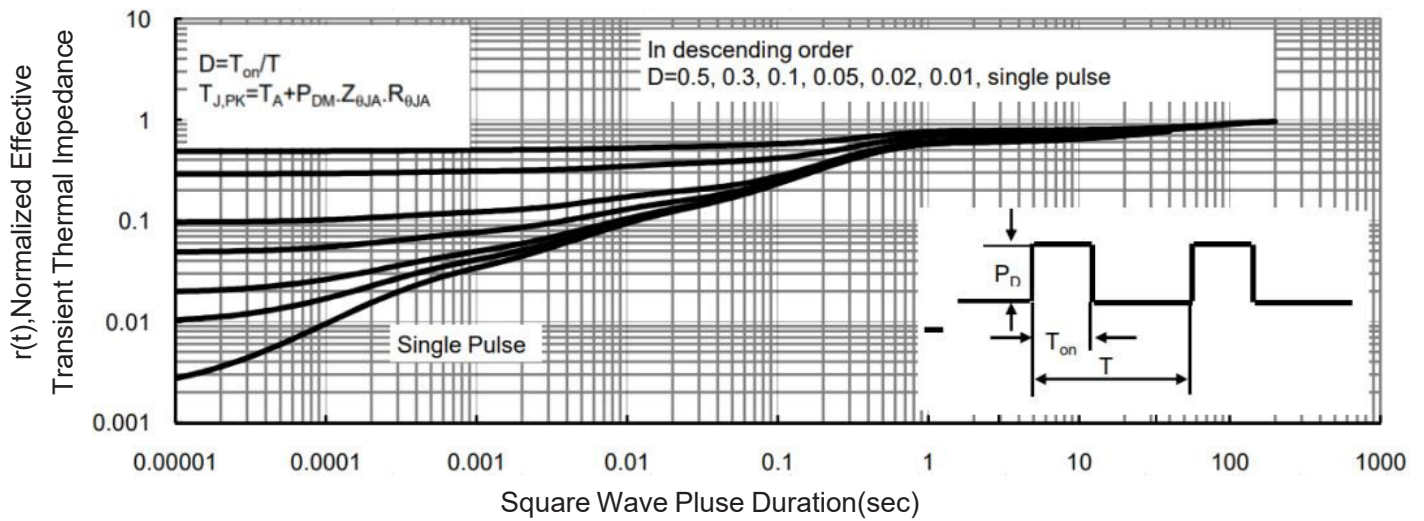


Figure 15 Normalized Maximum Transient Thermal Impedance